

ABSTRACT

A semiconductor single crystal manufacturing apparatus capable of lowering the local deterioration of a wire under high temperature atmosphere in the furnace of a chamber, wherein a crucible (24) in which silicon melt (28) is filled is installed in the furnace of the chamber (22), a pull-chamber (23) is disposed above the chamber (22), and a seed holder (32) lifting between the inside of the pull-chamber (23) and the inside of the furnace is suspended by a wire (50) through a coupling member (31). A collar (52) is fitted to the wire (50) so that, when the seed holder (32) is positioned to touch the melt, the exposed portion of the wire (50) near the tip thereof becomes a specified temperature or below under the high temperature atmosphere in the furnace.